TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process) Silicon PNP Epitaxial Type (PCT Process)

HN1B04FE

Audio Frequency General Purpose Amplifier Applications

Unit: mm

Q1:High voltage and high current

 $: V_{CEO} = 50V, I_{C} = 150mA (max)$

- High h_{FF} : h_{FF} = 120~400
- Excellent h_{FF} linearity

 $: h_{FE} (I_C = 0.1 \text{mA}) / h_{FE} (I_C = 2 \text{mA}) = 0.95 (typ.)$

Q2:

• High voltage and high current

 $: V_{CEO} = -50V, I_{C} = -150mA (max)$

- High h_{FE} : h_{FE} = 120~400
- Excellent h_{FE} linearity

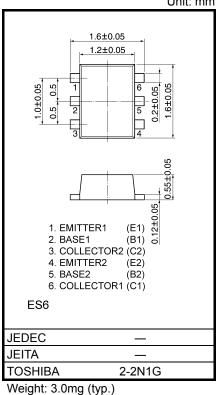
: $h_{FE} (I_C = -0.1 \text{mA}) / h_{FE} (I_C = -2 \text{mA}) = 0.95 (typ.)$

Q1 Absolute Maximum Ratings (Ta = 25°C)

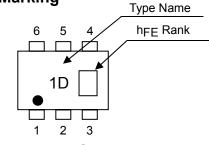
Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	Ι _C	150	mA
Base current	Ι _Β	30	mA

Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-150	mA
Base current	Ι _Β	-30	mA



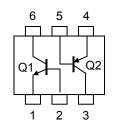
Marking



Equivalent Circuit (Top View)

Q1, Q2 Common Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	100	mW
Junction temperature	Тј	150	°C
Storage temperature range	T _{stg}	-55~150	°C



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

* Total rating

Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = 60V, I_E = 0$	_	_	0.1	μA
Emitter cut-off current	I _{EBO}	_	V _{EB} = 5V, I _C = 0		—	0.1	μA
DC current gain	h _{FE (Note)}	—	V _{CE} = 6V, I _C = 2mA	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = 100mA, I _B = 10mA	_	0.1	0.25	V
Transition frequency	f _T	_	V _{CE} = 10V, I _C = 1mA	80	—	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MHz		2		pF

Q2 Electrical Characteristics (Ta = 25°C)

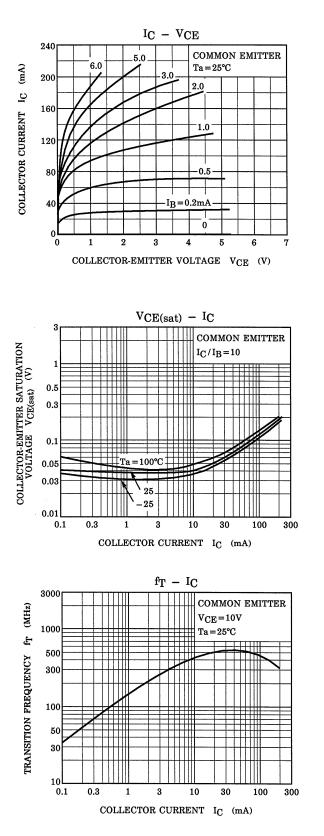
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = -50V, I_E = 0$	_	—	-0.1	μA
Emitter cut-off current	I _{EBO}	—	$V_{EB} = -5V, I_{C} = 0$		—	-0.1	μA
DC current gain	h _{FE (Note)}	_	$V_{CE} = -6V, I_C = -2mA$	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = −100mA, I _B = −10mA	_	-0.1	-0.3	V
Transition frequency	f _T	_	$V_{CE} = -10V, I_C = -1mA$	80	_	_	MHz
Collector output capacitance	C _{ob}	_	$V_{CB} = -10V, I_E = 0,$ f = 1MHz	_	4	_	pF

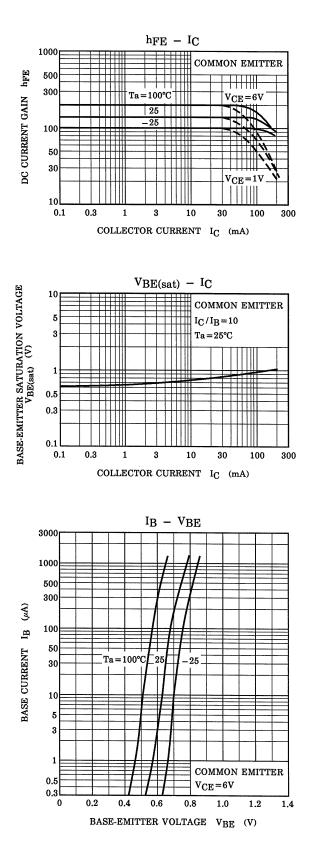
Note:h_{FE} Classification Y (Y): 120~240, GR (G): 200~400

() Marking Symbol

TOSHIBA

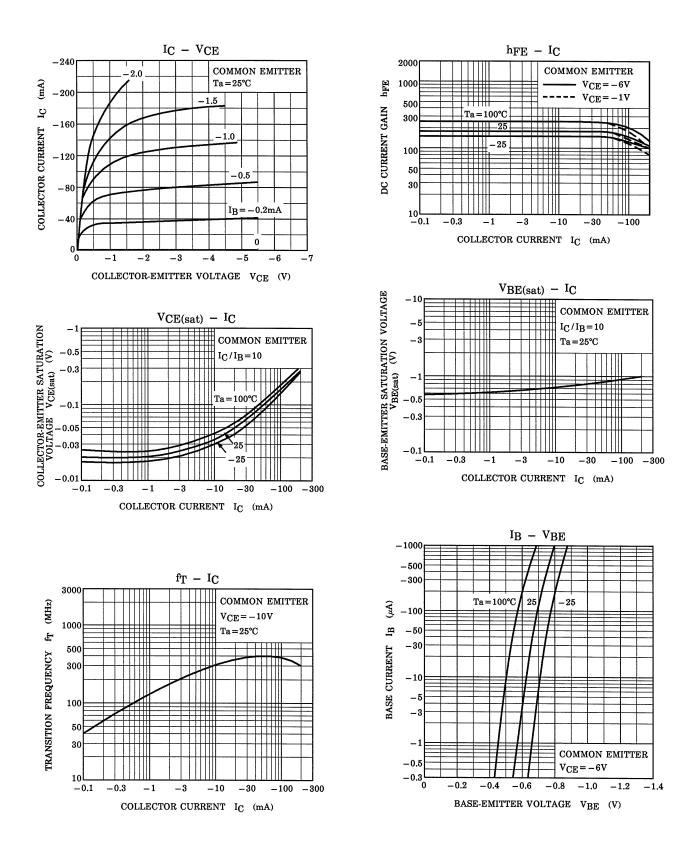
Q1 (NPN transistor)





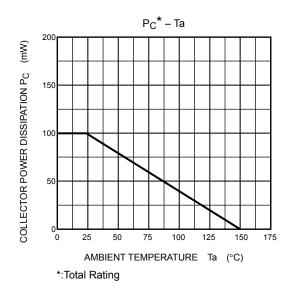
TOSHIBA

Q2 (PNP transistor)



TOSHIBA

(Q1, Q2 Common)



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20070701-EN GENERAL

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